

SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

Very Low-Power, Rail-to-Rail Out, Negative Rail In, VFB Op Amp

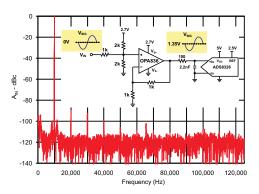
Check for Samples: OPA836, OPA2836

FEATURES

- Low Power:
 - Supply Voltage: 2.5 V to 5.5 V
 - Quiescent Current: 1 mA (Typ)
 - Power Down Mode: 0.5µA Ttyp)
- Bandwidth: 205 MHz
- Slew Rate: 560 V/µs
- Rise Time: 3 ns (2 V_{STEP})
- Settling Time: 22 ns (2 V_{STEP})
- **Overdrive Recovery Time: 60ns**
- SNR: 0.00013% (-117.6 dBc) at 1 kHz (1 V_{RMS})
- THD: 0.00003% (-130 dBc) at 1 kHz (1 V_{RMS}) .
- HD₂/HD₃: -85dBc / -105 dBc at 1 MHz (2 V_{PP})
- Input Voltage Noise: 4.6 nV/rtHz (f = 100 kHz)
- Input Offset Voltage: 65 µV (400 µV Max)
- **CMRR: 116 dB**
- **Output Current Drive: 50 mA**
- **RRO: Rail-to-Rail Output**
- Input Voltage Range: -0.2 V to 3.9 V (5 V Supply)
- **Operating Temperature Range:** -40°C to +125°C

APPLICATIONS

- Low Power Signal Conditioning
- Audio ADC Input Buffer
- Low Power SAR and $\Delta\Sigma$ ADC Driver
- **Portable Systems**
- Low Power Systems
- **High Density Systems**



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DESCRIPTION

Fabricated using the industry-leading BiCom-3x (SiGe complimentary bipolar) process, the OPA836 and OPA2836 are single and dual ultra low-power, rail-to-rail output, negative rail input, voltage-feedback operational amplifiers designed to operate over a power supply range of 2.5 V to 5.5 V Single Supply and ±1.25 V to ±2.75 V dual supply. Consuming only 1 mA per channel and a unity gain bandwidth of 205 MHz, these amplifiers set an industry leading powerto-performance ratio for rail-to-rail amplifiers.

For battery powered portable applications where power is of key importance, the OPA836's and OPA2836's low power consumption and high frequency performance offers designers performance versus power not attainable in other devices. Coupled with a power savings mode to reduce current to <1.5µA, the device offers an attractive solution for high frequency amplifiers in battery powered applications.

The OPA836 and OPA2836 are offered in following package options:

- OPA836 Single: SOT23-6 (DBV), and 10 pin WQFN (RUN) with integrated gain resistors.
- OPA2836 Dual: SOIC-8 (D), VSSOP (MSOP) -10 (DGS), 10 pin WQFN (RUN), and 10 pin UQFN (RMC).

The OPA836 RUN package option includes integrated gain setting resistors for smallest possible footprint on a printed circuit board (~ 2mm x 2mm). By adding circuit traces on the PCB, gains of +1, -1, -1.33, +2, +2.33, -3, +4, -4, +5, -5.33, +6.33, -7, +8 and inverting attenuations of -0.1429, -0.1875, -0.25, -0.33, -0.75 can be achieved. See the Application Information section for details.

The devices are characterized for operation over the extended industrial temperature range -40°C to 125°C.

OPA	836 Rela	ited Proc	lucts	
DESCRIPTION	SINGLES	DUALS	TRIPLES	QUADS
Rail-to-Rail		OPA2830		OPA4830
Rail-to-Rail, Low Power	OPA835	OPA2835		—
Rail-to-Rail, Fixed Gain	OPA832	OPA2832	OPA3832	—
General-Purpose, High Slew Rate	OPA690	OPA2690	OPA3690	—
Low-Noise, DC Precision	OPA820	OPA2822	_	OPA4820

DA926 Deleted Broducto

OPA836 OPA2836



SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGING/ORDERING INFORMATION⁽¹⁾

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

			UNITS
$V_{\text{S-}}$ to $V_{\text{S+}}$	Supply volt	age	5.5
VI	Input volta	ge	V_{S-} - 0.7V to V_{S+} + 0.7V
V _{ID}	Differential	input voltage	1 V
I _I	Continuous	s input current	0.85 mA
I _O	Continuous output current		60 mA
	Continuous power dissipation		See Thermal Characteristics Specification
TJ	Maximum j	unction temperature	150°C
T _A	Operating f	ree-air temperature range	–40°C to 125°C
T _{stg}	Storage ter	nperature range	–65°C to 150°C
		НВМ	6 kV
	ESD ratings	CDM	1 kV
		MM	200 V

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		OP	A836					
		SOT23-6 (DBV)	WQFN-10 (RUN)	SOIC-8 (D)	VSSOP (MSOP)-10 (DGS)	WQFN-10 (RUN)	UQFN-10 (RMC)	UNITS
		6 PINS	10 PINS	8 PINS	10 PINS	10 PINS	10 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	194	145.8	150.1	206	145.8	143.2	
θ_{JCtop}	Junction-to-case (top) thermal resistance	129.2	75.1	83.8	75.3	75.1	49.0	
θ_{JB}	Junction-to-board thermal resistance	39.4	38.9	68.4	96.2	38.9	61.9	°C/W
ΨJT	Junction-to-top characterization parameter	25.6	13.5	33.0	12.9	13.5	3.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	38.9	104.5	67.9	94.6	104.5	61.9	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	n/a	n/a	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



www.ti.com

SPECIFICATIONS: $V_S = 2.7 V$

Test conditions unless otherwise noted: $V_{S+} = +2.7 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 1 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN TYP M	AX UNITS	TEST LEVEL ⁽¹⁾
AC PERFORMANCE	I			
	V _{OUT} = 100 mV _{PP} , G = 1	200		
	V _{OUT} = 100 mV _{PP} , G = 2	100	MI 1-	0
Small-signal bandwidth	V _{OUT} = 100 mV _{PP} , G = 5	26	MHz	С
	V _{OUT} = 100 mV _{PP} , G = 10	11		
Gain-bandwidth product	V _{OUT} = 100 mV _{PP} , G = 10	110	MHz	С
Large-signal bandwidth	$V_{OUT} = 1 V_{PP}, G = 2$	60	MHz	С
Bandwidth for 0.1dB flatness	V _{OUT} = 1 V _{PP} , G=2	25	MHz	С
Slew rate, Rise/Fall		260/240	V/µs	С
Rise/Fall time		4/4.5	ns	С
Settling time to 1%, Rise/Fall		15/15	ns	С
Settling time to 0.1%, Rise/Fall	$V_{OUT} = 1V_{STEP}, G = 2$	30/25	ns	С
Settling time to 0.01%, Rise/Fall		50/45	ns	С
Overshoot/Undershoot		5/3	%	С
	$f = 10 \text{ kHz}, V_{IN_{CM}} = \text{mid-supply} - 0.5V$	-133		С
2 nd Order Harmonic Distortion	f = 100 kHz, V_{IN_CM} = mid-supply - 0.5V	-120	dBc	С
	$f = 1 \text{ MHz}, V_{IN_CM} = mid-supply - 0.5V$	-84		С
	$f = 10 \text{ kHz}, V_{IN_CM} = mid-supply - 0.5V$	-137		С
3 rd Order Harmonic Distortion	$f = 100 \text{ kHz}, V_{IN_CM} = \text{mid-supply} - 0.5V$	-130	dBc	С
	f = 1 MHz, V_{IN_CM} = mid-supply – 0.5V	-105		С
2 nd Order Intermodulation Distortion	f = 1 MHz, 200 kHz Tone Spacing, V _{OUT}	-90	dBc	С
3 rd Order Intermodulation Distortion	Envelope = 1V _{PP} , V _{IN_CM} = mid-supply – 0.5V	-90	dBc	С
Input voltage noise	f = 100 KHz	4.6	nV/√Hz	С
Voltage Noise 1/f corner frequency		215	Hz	С
Input current noise	f = 1 MHz	0.75	pA/√Hz	С
Current Noise 1/f corner frequency		31.7	kHz	С
Overdrive recovery time, Over/Under	Overdrive = 0.5 V	55/60	ns	С
Closed-loop output impedance	f = 100 kHz	0.02	Ω	С
Channel to channel crosstalk (OPA2836)	f = 10 kHz	-120	dB	С

(1) Test levels (all values set by characterization and simulation): (A) 100% tested at 25°C; over temperature limits by characterization and simulation. (B) Not tested in production; limits set by characterization and simulation. (C) Typical value only for information.



www.ti.com

SPECIFICATIONS: V_s = 2.7 V

Test conditions unless otherwise noted: $V_{S+} = +2.7 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 1 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNITS	TEST LEVEL ⁽¹⁾
DC PERFORMANCE						
Open-loop voltage gain (A _{OL})		100	125		dB	А
	$T_A = 25^{\circ}C$		±65	±400		А
Innut referred offect voltoge	$T_A = 0^{\circ}C$ to $70^{\circ}C$			±680		
Input referred offset voltage	$T_A = -40^{\circ}C$ to $85^{\circ}C$			±760	μV	В
	$T_A = -40^{\circ}C$ to 125°C			±1060		
	$T_A = 0^{\circ}C$ to $70^{\circ}C$		±1	±6.2		
Input offset voltage drift ⁽²⁾	$T_A = -40^{\circ}C$ to $85^{\circ}C$		±1	±6	µV/°C	В
	$T_A = -40^{\circ}C$ to 125°C		±1.1	±6.6		
	$T_A = 25^{\circ}C$	300	650	1000		Α
	$T_A = 0^{\circ}C$ to $70^{\circ}C$	190		1400		
Input bias current	$T_A = -40^{\circ}C \text{ to } 85^{\circ}C$	120		1500	nA	В
	$T_A = -40^{\circ}C$ to 125°C	120		1800		
	$T_A = 0^{\circ}C$ to $70^{\circ}C$		±0.33	±2		
Input bias current drift ⁽²⁾	$T_A = -40^{\circ}C \text{ to } 85^{\circ}C$		±0.32	±1.9	nA/°C	В
	$T_A = -40^{\circ}C$ to 125°C		±0.37	±2.1		
	$T_A = 25^{\circ}C$		±30	±180		А
	$T_A = 0^{\circ}C$ to $70^{\circ}C$		±30	±200		
Input offset current	$T_A = -40^{\circ}C$ to $85^{\circ}C$		±30	±215	nA	В
	$T_A = -40^{\circ}C$ to 125°C		±30	±240		
	$T_A = 0^{\circ}C$ to $70^{\circ}C$		±77	±460		
Input offset current drift ⁽²⁾	$T_A = -40^{\circ}C \text{ to } 85^{\circ}C$		±95	±575	pA/°C	В
	$T_A = -40^{\circ}C$ to $125^{\circ}C$		±100	±600		
INPUT	•					
	$T_A = 25^{\circ}C$, <3dB degradation in CMRR limit		-0.2	0	V	А
Common-mode input range low	$T_A = -40^{\circ}C$ to 125°C, <3dB degradation in CMRR limit		-0.2	0	V	В
	$T_A = 25^{\circ}C$, <3dB degradation in CMRR limit	1.5	1.6		V	А
Common-mode input range high	$T_A = -40^{\circ}C$ to 125°C, <3dB degradation in CMRR limit	1.5	1.6		V	В
Input linear operating voltage range	$T_A = 25^{\circ}C$, <6dB degradation in THD		-0.3 to 1.75		V	С
Common-mode rejection ratio		91	114		dB	А
Input impedance common mode			200 1.2		kΩ ∥ pF	С
Input impedance differential mode			200 1		kΩ ∥ pF	С
OUTPUT						
	$T_A = 25^{\circ}C, G = 5$		0.15	0.2	V	А
Linear output voltage low	$T_A = -40^{\circ}C$ to 125°C, G = 5		0.15	0.2	V	В
	T _A = 25°C, G = 5	2.45	2.5		V	А
Linear output voltage high	$T_A = -40^{\circ}C$ to 125°C, G = 5	2.45	2.5		V	В
Output saturation voltage, High / Low	$T_A = 25^{\circ}C, G = 5$		80/40		mV	С
	T _A = 25°C	±40	±45		mA	А
Linear output current drive	$T_A = -40^{\circ}C$ to 125°C	±40	±45		mA	В

(1) Test levels (all values set by characterization and simulation): (A) 100% tested at 25°C; over temperature limits by characterization and simulation. (B) Not tested in production; limits set by characterization and simulation. (C) Typical value only for information. Input Offset Voltage Drift, Input Bias Current Drift, and Input Offset Current Drift are average values calculated by taking data at the end

(2) points, computing the difference, and dividing by the temperature range.



www.ti.com

SPECIFICATIONS: V_s = 2.7 V (continued)

Test conditions unless otherwise noted: $V_{S+} = +2.7 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 1 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNITS	TEST LEVEL ⁽¹⁾
GAIN SETTING RESISTORS (OPA8	36IRUN ONLY)					
Resistor FB1 to FB2	DC resistance	1584	1600	1616	Ω	А
Resistor FB2 to FB3	DC resistance	1188	1200	1212	Ω	А
Resistor FB3 to FB4	DC resistance	396	400	404	Ω	A
Resistor Tolerance	DC resistance			±1	%	A
Resistor Temperature Coefficient	DC resistance		<10		PPM	С
POWER SUPPLY						
Specified operating voltage		2.5		5.5	V	В
Quiescent operating current per	T _A = 25°C	0.7	0.95	1.15	mA	A
amplifer	$T_A = -40^{\circ}C$ to $125^{\circ}C$	0.6		1.4	mA	В
Power supply rejection (±PSRR)		91	108		dB	A
POWER DOWN						
Enable voltage threshold	Specified "on" above V _{S-} + 2.1 V			2.1	V	А
Disable voltage threshold	Specified "off" below V _{S-} + 0.7 V	0.7			V	А
Powerdown pin bias current	PD = 0.5 V		20	500	nA	А
Powerdown quiescent current	PD = 0.5 V		0.5	1.5	μΑ	А
Turn-on time delay	Time from \overline{PD} = high to V _{OUT} = 90% of final value		200		ns	С
Turn-off time delay	Time from \overline{PD} = low to V _{OUT} = 10% of original value		25		ns	С



www.ti.com

SPECIFICATIONS: V_s = 5 V

Test conditions unless otherwise noted: $V_{S+} = +5 V$, $V_{S-} = 0V$, $V_{OUT} = 2 V_{PP}$, $R_F = 0 \Omega$, $R_L = 1 k\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}C$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN TYP	МАХ	UNITS	TEST LEVEL ⁽¹⁾
AC PERFORMANCE					
	V _{OUT} = 100 mV _{PP} , G = 1	205			
	V _{OUT} = 100 mV _{PP} , G = 2	100			
Small-signal bandwidth	V _{OUT} = 100 mV _{PP} , G = 5	28		MHz	С
	V _{OUT} = 100 mV _{PP} , G = 10	11.8			
Gain-bandwidth product	V _{OUT} = 100 mV _{PP} , G = 10	118		MHz	С
Large-signal bandwidth	V _{OUT} = 2 V _{PP} , G = 2	87		MHz	С
Bandwidth for 0.1dB flatness	V _{OUT} = 2 V _{PP} , G = 2	29		MHz	С
Slew rate, Rise/Fall		560/580		V/µs	С
Rise/Fall time		3/3		ns	С
Settling time to 1%, Rise/Fall		22/22		ns	С
Settling time to 0.1%, Rise/Fall	$V_{OUT} = 2V$ Step, G = 2	30/30		ns	С
Settling time to 0.01%, Rise/Fall		40/45		ns	С
Overshoot/Undershoot		7.5/5		%	С
	f = 10 kHz	-133			С
2 nd Order Harmonic Distortion	f = 100 kHz	-120		dBc	С
	f = 1 MHz	-85			С
	f = 10 kHz	-140			С
3 rd Order Harmonic Distortion	f = 100 kHz	-130		dBc	С
	f = 1 MHz	-105			С
2 nd Order Intermodulation Distortion	f = 1 MHz, 200 kHz Tone Spacing,	-79		dBc	С
3 rd Order Intermodulation Distortion	V_{OUT} Envelope = $2V_{PP}$	-91		dBc	С
	f = 1kHz, V _{OUT} = 1 V _{RMS} , 22kHz	0.00013		%	С
Signal to Noise Ratio, SNR	bandwidth	-117.6		dBc	С
		0.00003		%	С
Total Harmonic Distortion, THD	$f = 1 kHz$, $V_{OUT} = 1 V_{RMS}$	-130		dBc	С
Input voltage noise	f = 100 KHz	4.6		nV/√Hz	С
Voltage Noise 1/f corner frequency		215		Hz	С
Input current noise	f > 1 MHz	0.75		pA/√Hz	С
Current Noise 1/f corner frequency		31.7		kHz	С
Overdrive recovery time, Over/Under	Overdrive = 0.5 V	55/60		ns	С
Closed-loop output impedance	f = 100 kHz	0.02		Ω	С
Channel to channel crosstalk (OPA2836)	f = 10 kHz	-120		dB	С

(1) Test levels (all values set by characterization and simulation): (A) 100% tested at 25°C; over temperature limits by characterization and simulation. (B) Not tested in production; limits set by characterization and simulation. (C) Typical value only for information.



www.ti.com

SPECIFICATIONS: $V_s = 5 V$

Test conditions unless otherwise noted: $V_{S+} = +5 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 2 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}\text{C}$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNITS	TEST LEVEL ⁽¹⁾
DC PERFORMANCE						
Open-loop voltage gain (A _{OL})		100	122		dB	А
	$T_A = 25^{\circ}C$		±65			А
	$T_A = 0^{\circ}C$ to $70^{\circ}C$			±685		
Input referred offset voltage	$T_A = -40^{\circ}C \text{ to } 85^{\circ}C$			±765	μV	В
	$T_A = -40^{\circ}C$ to 125°C			±1080		
	$T_A = 0^{\circ}C$ to 70°C		±1.05	±6.3		
Input offset voltage drift ⁽²⁾	$T_A = -40^{\circ}C$ to $85^{\circ}C$		±1	±6.1	µV/°C	В
	$T_A = -40^{\circ}C$ to 125°C		±1.1	±6.8		
	$T_A = 25^{\circ}C$	300	650	1000		А
	$T_A = 0^{\circ}C$ to 70°C	190		1400		
Input bias current	$T_A = -40^{\circ}C$ to $85^{\circ}C$	120		1550	nA	В
	$T_A = -40^{\circ}C$ to 125°C	120		1850		
	$T_A = 0^{\circ}C$ to 70°C		±0.34	±2		
Input bias current drift ⁽²⁾	$T_A = -40^{\circ}C$ to $85^{\circ}C$		±0.34	±2	nA/°C	В
	$T_A = -40^{\circ}C$ to 125°C		±0.38	±2.3		
	T _A = 25°C		±30	±180		А
	$T_A = 0^{\circ}C$ to 70°C		±30	±200		
Input offset current	$T_A = -40^{\circ}C \text{ to } 85^{\circ}C$		±30	±215	nA	В
	$T_A = -40^{\circ}C$ to 125°C		±30	±250		
	$T_A = 0^{\circ}C$ to 70°C		±80	±480		
Input offset current drift ⁽²⁾	$T_A = -40^{\circ}C$ to 85°C		±100	±600	pA/°C	В
	$T_A = -40^{\circ}C$ to 125°C		±110	±660	1	
INPUT						
	$T_A = 25^{\circ}C$, <3dB degradation in CMRR limit		-0.2	0	V	A
Common-mode input range low	$T_A = -40^{\circ}$ C to 125°C, <3dB degradation in CMRR limit		-0.2	0	V	В
	$T_A = 25^{\circ}C$, <3dB degradation in CMRR limit	3.8	3.9		V	А
Common-mode input range high	$T_A = -40^{\circ}$ C to 125°C, <3dB degradation in CMRR limit	3.8	3.9		V	В
Input linear operating voltage range	$T_A = 25^{\circ}C$, <6dB degradation in THD		-0.3 to 4.05		V	С
Common-mode rejection ratio		94	116		dB	А
Input impedance common mode			200 1.2		kΩ ∥ pF	С
Input impedance differential mode			200 1		kΩ pF	С
OUTPUT						
	T _A = 25°C, G =		0.15	0.2	V	А
Linear output voltage low	$T_A = -40^{\circ}C$ to 125°C, G = 5		0.15	0.2	V	В
	$T_{A} = 25^{\circ}C, G = 5$	4.75	4.8		V	A
Linear output voltage high	$T_A = -40^{\circ}$ C to 125°C, G = 5	4.75	4.8		V	В
Output saturation voltage, High / Low	$T_{A} = 25^{\circ}C, G = 5$		100/50		mV	C
	$T_A = 25^{\circ}$ C	±40	±50		mA	A
Linear output current drive	· A •	2.10	700			

Test levels (all values set by characterization and simulation): (A) 100% tested at 25°C; over temperature limits by characterization and simulation. (B) Not tested in production; limits set by characterization and simulation. (C) Typical value only for information.

(2) Input Offset Voltage Drift, Input Bias Current Drift, and Input Offset Current Drift are average values calculated by taking data at the end points, computing the difference, and dividing by the temperature range.



www.ti.com

SPECIFICATIONS: $V_s = 5 V$ (continued)

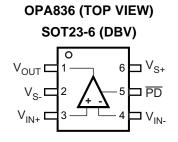
Test conditions unless otherwise noted: $V_{S+} = +5 V$, $V_{S-} = 0 V$, $V_{OUT} = 2 V_{PP}$, $R_F = 0 \Omega$, $R_L = 1 k\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply. $T_A = 25^{\circ}C$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNITS	TEST LEVEL ⁽¹⁾
GAIN SETTING RESISTORS (OPA	B36IRUN ONLY)					
Resistor FB1 to FB2	DC resistance	1584	1600	1616	Ω	А
Resistor FB2 to FB3	DC resistance	1188	1200	1212	Ω	А
Resistor FB3 to FB4	DC resistance	396	400	404	Ω	А
Resistor Tolerance	DC resistance			±1	%	А
Resistor Temperature Coefficient	DC resistance		<10		PPM	С
POWER SUPPLY						
Specified operating voltage		2.5		5.5	V	В
Quiescent operating current per	$T_A = 25^{\circ}C$	0.8	1.0	1.2	mA	А
amplifier	$T_A = -40^{\circ}C$ to 125°C	0.65		1.5	mA	В
Power supply rejection (±PSRR)		94	108		dB	А
POWER DOWN						
Enable voltage threshold	Specified "on" above V _{S-} + 2.1 V			2.1	V	А
Disable voltage threshold	Specified "off" below V _{S-} + 0.7 V	0.7			V	А
Powerdown pin bias current	PD = 0.5 V		20	500	nA	А
Powerdown quiescent current	PD = 0.5 V		0.5	1.5	μA	А
Turn-on time delay	Time from \overline{PD} = high to V _{OUT} = 90% of final value		170		ns	С
Turn-off time delay	Time from \overline{PD} = low to V _{OUT} = 10% of original value		35		ns	С



DEVICE INFORMATION

PIN CONFIGURATIONS



OPA2836 (TOP VIEW)

SOIC-8 (D)

⊐v_{s+}

V_{OUT2}

V_{IN2-}

V_{IN2+}

8

0

V_{OUT1} ⊏

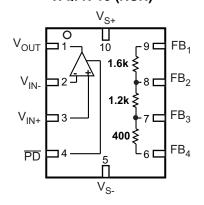
V_{IN1-} ⊏

V_{S-} - 4

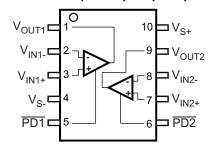
 V_{IN1+}

OPA836 (TOP VIEW) WQFN-10 (RUN)

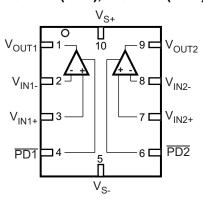
SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013



OPA2836 (TOP VIEW) VSSOP (MSOP)-10 (DGS)



OPA2836 (TOP VIEW) WQFN-10 (RUN), UQFN-10 (RMC)



www.ti.com

NSTRUMENTS

Texas

PIN FUNCTIONS				
PIN DESCRIPTION				
NUMBER	NAME	DESCRIPTION		
OPA836 DBV PA	CKAGE			
1	V _{OUT}	Amplifier output		
2	V _{S-}	Negative power supply input		
3	V _{IN+}	Amplifier non-inverting input		
4	V _{IN-}	Amplifier inverting input		
5	PD	Amplifier Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)		
6	V _{S+}	Positive power supply input		
OPA836 RUN PA	CKAGE			
1	V _{OUT}	Amplifier output		
2	V _{IN}	Amplifier inverting input		
3	V _{IN+}	Amplifier non-inverting input		
4	PD	Amplifier Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)		
5	V _{S-}	Negative power supply input		
6	FB_4	Connection to bottom of 250 Ω internal gain setting resistors		
7	FB ₃	Connection to junction of 750 and 250 Ω internal gain setting resistors		
8	FB_2	Connection to junction of 1k and 750 Ω internal gain setting resistors		
9	FB ₁	Connection to top of $1k\Omega$ internal gain setting resistors		
10	V _{S+}	Positive power supply input		
OPA2836 D PAC	KAGE			
1	V _{OUT1}	Amplifier 1 output		
2	V _{IN1-}	Amplifier 1 inverting input		
3	V _{IN1+}	Amplifier 1 non-inverting input		
4	V _{S-}	Negative power supply input		
5	V _{IN2+}	Amplifier 2 non-inverting input		
6	V _{IN2-}	Amplifier 2 inverting input		
7	V _{OUT2}	Amplifier 2 output		
8	V _{S+}	Positive power supply input		
OPA2836 DSG P				
1	V _{OUT1}	Amplifier 1 output		
2	V _{IN1-}	Amplifier 1 inverting input		
3	V _{IN1+}	Amplifier 1 non-inverting input		
4	V _S _	Negative power supply input		
5	PD1	Amplifier 1 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)		
6	PD2	Amplifier 2 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)		
7	V _{IN2+}	Amplifier 2 non-inverting input		
8	V _{IN2}	Amplifier 2 inverting input		
9	V _{OUT2}	Amplifier 2 output		
10	V _{S+}	Positive power supply input		



www.ti.com

PIN FUNCTIONS (continued)

PIN		DESCRIPTION						
NUMBER	NAME	DESCRIPTION						
OPA2836 RUN	OPA2836 RUN AND RMC PACKAGES							
1	V _{OUT1}	Amplifier 1 output						
2	V _{IN1-}	Amplifier 1 inverting input						
3	V _{IN1+}	Amplifier 1 non-inverting input						
4	PD1	Amplifier 1 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)						
5	V _{S-}	Negative power supply input						
6	PD2	Amplifier 2 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)						
7	V _{IN2+}	Amplifier 2 non-inverting input						
8	V _{IN2-}	Amplifier 2 inverting input						
9	V _{OUT2}	Amplifier 2 output						
10	V _{S+}	Positive power supply input						

TYPICAL PERFORMANCE GRAPHS: $V_s = 2.7 V$

Test conditions unless otherwise noted: $V_{S+} = +2.7 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 1 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply unless otherwise noted. $T_A = 25^{\circ}\text{C}$.

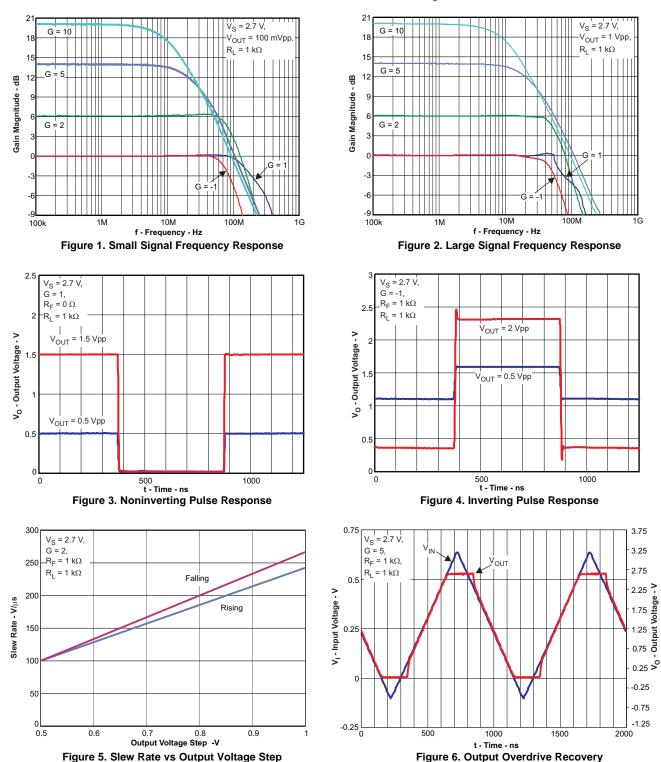
Table of Graphs

		FIGURES
Small Signal Frequency Response		Figure 1
Large Signal Frequency Response		Figure 2
Noninverting Pulse Response		Figure 3
Inverting Pulse Response		Figure 4
Slew rate	vs Output Voltage Step	Figure 5
Output Overdrive Recovery		Figure 6
Harmonic Distortion	vs Frequency	Figure 7
Harmonic Distortion	vs Load Resistance	Figure 8
Harmonic Distortion	vs Output Voltage	Figure 9
Harmonic Distortion	vs Gain	Figure 10
Output Voltage Swing	vs Load Resistance	Figure 11
Output Saturation Voltage	vs Load Current	Figure 12
Output Impedance	vs Frequency	Figure 13
Frequency Response with Capacitive Load		Figure 14
Series Output Resistor	vs Capacitive Load	Figure 15
Input Referred Noise	vs Frequency	Figure 16
Open Loop Gain	vs Frequency	Figure 17
Common Mode/Power Supply Rejection Ratios	vs Frequency	Figure 18
Crosstalk	vs Frequency	Figure 19
Power Down Response		Figure 20
Input Offset Voltage		Figure 21
Input Offset Voltage	vs Free-Air Temperature	Figure 22
Input Offset Voltage Drift		Figure 49
Input Offset Current		Figure 24
Input Offset Current	vs Free-Air Temperature	Figure 25
Input Offset Current Drift		Figure 26



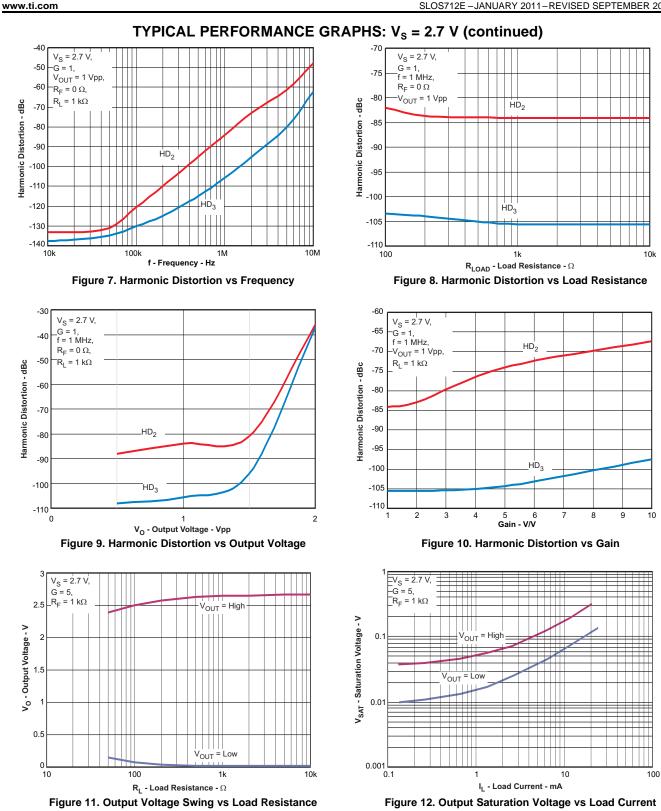
www.ti.com











100 -G = 1

10

0.1

0.01

100

 ${f R}_{f O}$ - Output Resistor - Ω

10

1

TTT

Ш

Open Loop

Gair

140

130

120

110

100

90

80

70

60

50

40

30

0 -10

-20

-30

-40

1

10

100

1k

10k

100k

Figure 17. Open Loop Gain vs Frequency

f - Frequency - Hz

1M

10M

100M

- Magnitude - dB

Å 20 10

10k

V_S = 2.7 V,

-R_L = 1 kΩ

-G = 1 _R_F = 0 Ω,

 $\mathbf{Z}_{\mathbf{O}}$ - Output Impedance - Ω

_V_S = 2.7 V,



 C_L

40.2 Ω

1G

R_O

C_L = 10 pF

100M

Voltage Noise

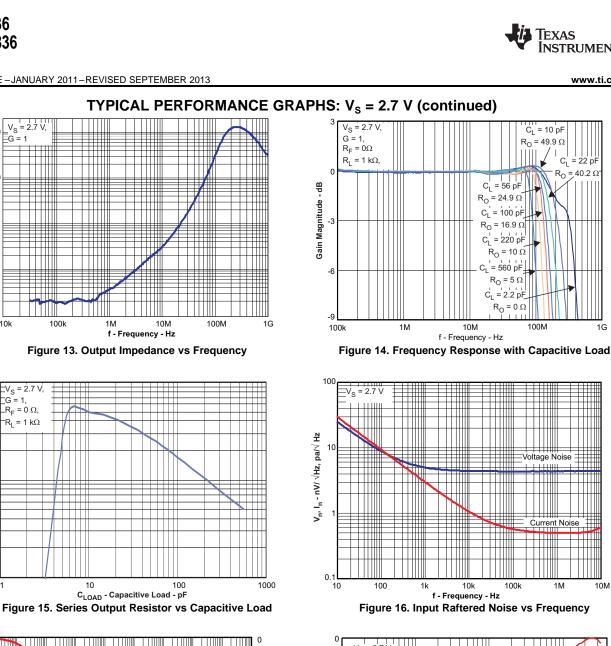
Current Noise

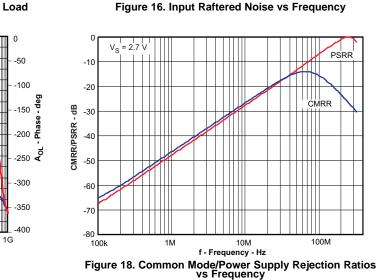
1M

10M

SLOS712E - JANUARY 2011-REVISED SEPTEMBER 2013

www.ti.com





Open Loop Gain Magnitude

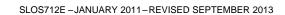


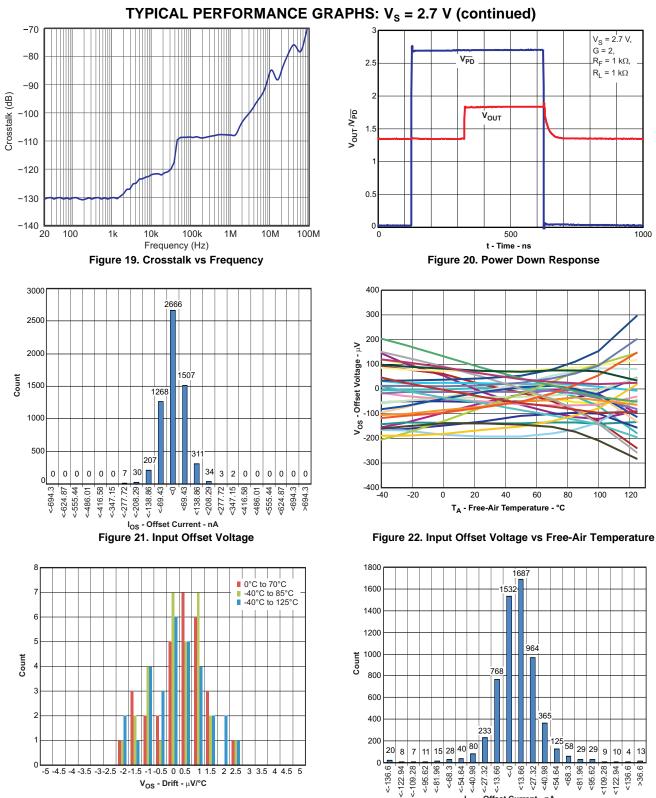
V_S = 2.7 V, G = 2,

R_F = 1 kΩ,

 $R_L = 1 k\Omega$

1000





I_{OS} - Offset Current - nA Figure 24. Input Offset Current

Figure 23. Input Offset Voltage Drift

58 29 29

<68.3 <81.96 <95.62 <109.28 <122.94 <136.6

9 10 4

>36.6

80

100

120



SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

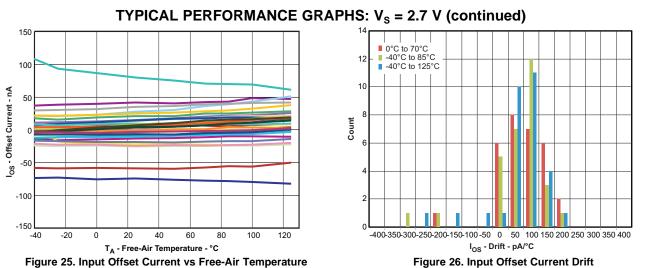


Figure 26. Input Offset Current Drift



SLOS712E – JANUARY 2011 – REVISED SEPTEMBER 2013

TYPICAL PERFORMANCE GRAPHS: $V_s = 5 V$

Test conditions unless otherwise noted: $V_{S+} = +5 \text{ V}$, $V_{S-} = 0 \text{ V}$, $V_{OUT} = 2 \text{ V}_{PP}$, $R_F = 0 \Omega$, $R_L = 1 \text{ k}\Omega$, G = 1 V/V, Input and Output Referenced to mid-supply unless otherwise noted. $T_A = 25^{\circ}\text{C}$.

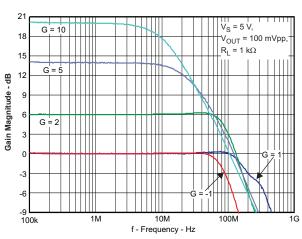
Table of Graphs

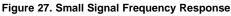
		FIGURES
Small Signal Frequency Response		Figure 27
Large Signal Frequency Response		Figure 28
Noninverting Pulse Response		Figure 29
Inverting Pulse Response		Figure 30
Slew rate	vs Output Voltage Step	Figure 31
Output Overdrive Recovery		Figure 32
Harmonic Distortion	vs Frequency	Figure 33
Harmonic Distortion	vs Load Resistance	Figure 34
Harmonic Distortion	vs Output Voltage	Figure 35
Harmonic Distortion	vs Gain	Figure 36
Output Voltage Swing	vs Load Resistance	Figure 37
Output Saturation Voltage	vs Load Current	Figure 38
Output Impedance	vs Frequency	Figure 39
Frequency Response with Capacitive Load		Figure 40
Series Output Resistor	vs Capacitive Load	Figure 41
Input Referred Noise	vs Frequency	Figure 42
Open Loop Gain	vs Frequency	Figure 43
Common Mode/Power Supply Rejection Ratios	vs Frequency	Figure 44
Crosstalk	vs Frequency	Figure 45
Power Down Response		Figure 46
Input Offset Voltage		Figure 47
Input Offset Voltage	vs Free-Air Temperature	Figure 48
Input Offset Voltage Drift		Figure 49
Input Offset Current		Figure 50
Input Offset Current	vs Free-Air Temperature	Figure 51
Input Offset Current Drift		Figure 52

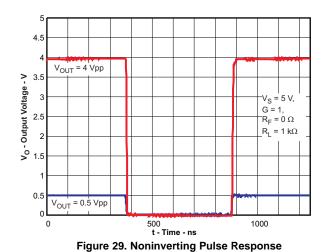


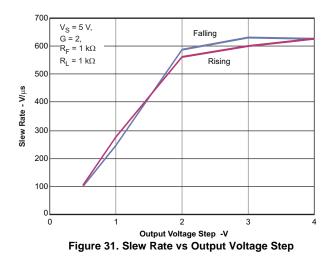
www.ti.com

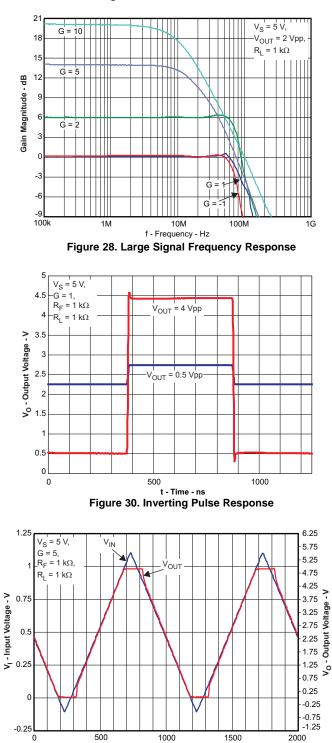












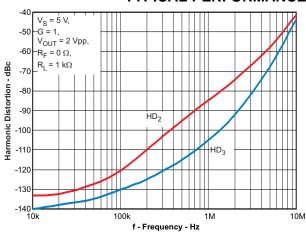
t - Time - ns

Figure 32. Output Overdrive Recovery

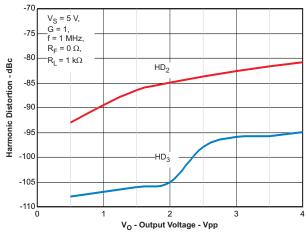


SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

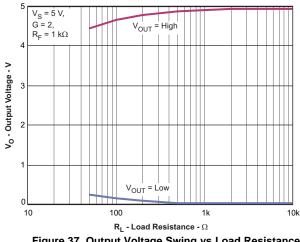
TYPICAL PERFORMANCE GRAPHS: V_s = 5 V (continued)

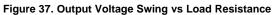


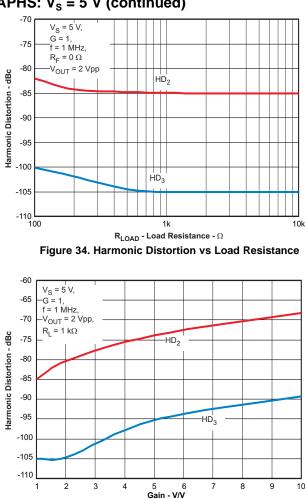














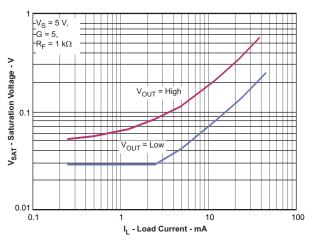
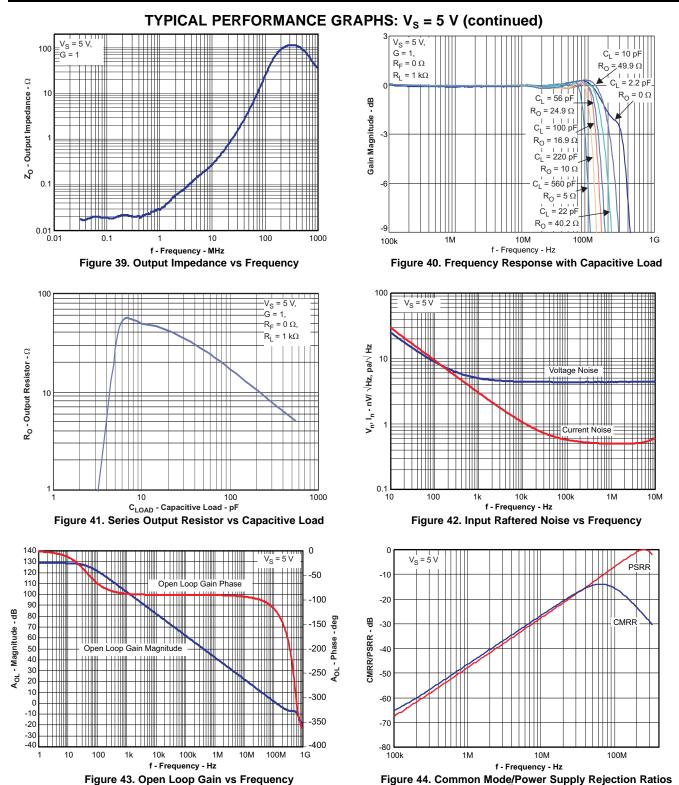


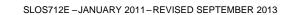
Figure 38. Output Saturation Voltage vs Load Current



www.ti.com







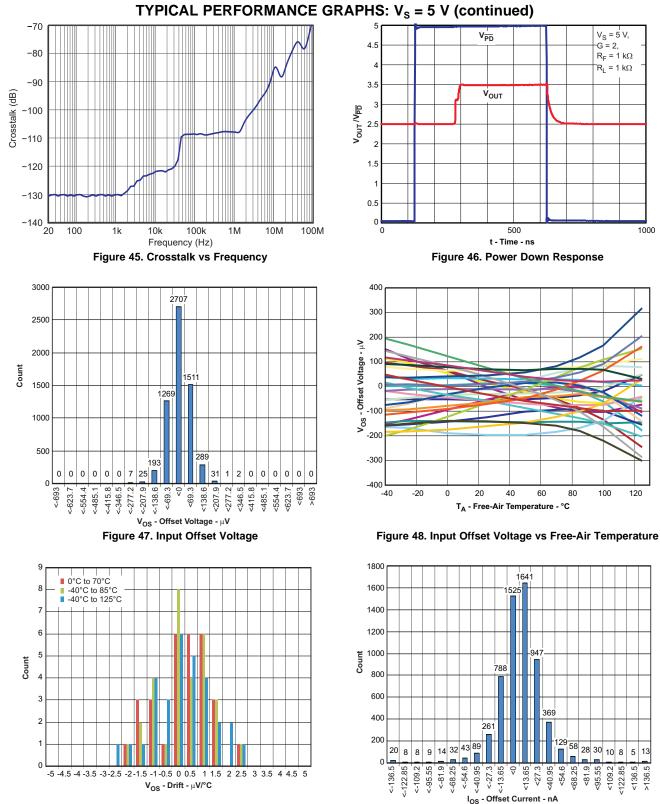


Figure 49. Input Offset Voltage Drift

Figure 50. Input Offset Current

l_{OS} - Offset Current - nA



SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

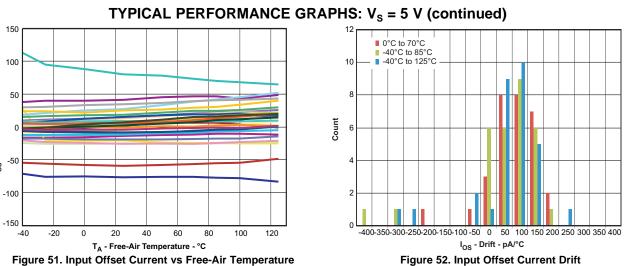


Figure 51. Input Offset Current vs Free-Air Temperature

www.ti.com



APPLICATION INFORMATION

The following circuits show application information for the OPA836 and OPA2836. For simplicity, power supply decoupling capacitors are not shown in these diagrams.

Non-Inverting Amplifier

The OPA836 and OPA2836 can be used as non-inverting amplifiers with signal input to the non-inverting input, V_{IN+} . A basic block diagram of the circuit is shown in Figure 53.

If we set $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT} = V_{SIG} \left(1 + \frac{R_F}{R_G} \right) + V_{REF}$$
(1)

$$G = 1 + \frac{R_F}{D}$$

The signal gain of the circuit is set by: R_G , and V_{REF} provides a reference around which the input and output signals swing. Output signals are in-phase with the input signals.

The OPA836 and OPA2836 are designed for the nominal value of R_F to be $1k\Omega$ in gains other than +1. This gives excellent distortion performance, maximum bandwidth, best flatness, and best pulse response. $R_F = 1k\Omega$ should be used as a default unless other design goals require changing to other values All test circuits used to collect data for this data sheet had $R_F = 1k\Omega$ for all gains other than +1. Gain of +1 is a special case where R_F is shorted and R_G is left open.

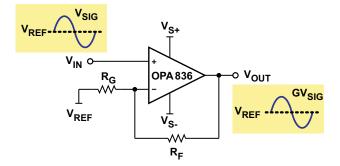


Figure 53. Non-Inverting Amplifier

Inverting Amplifier

The OPA836 and OPA2836 can be used as inverting amplifiers with signal input to the inverting input, V_{IN-} , through the gain setting resistor R_G . A basic block diagram of the circuit is shown in Figure 54.

If we set $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT} = V_{SIG} \left(\frac{-R_F}{R_G} \right) + V_{REF}$$

(2)

 $G = \frac{-R_F}{R_P}$

The signal gain of the circuit is set by: R_G and V_{REF} provides a reference point around which the input and output signals swing. Output signals are 180° out-of-phase with the input signals. The nominal value of R_F should be 1k Ω for inverting gains.



www.ti.com

(3)

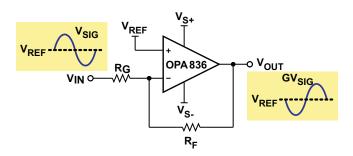


Figure 54. Inverting Amplifier

Attenuators

The non-inverting circuit of Figure 53 has minimum gain of 1. To implement attenuation, a resistor divider can be placed in series with the positive input, and the amplifier set for gain of 1 by shorting V_{OUT} to V_{IN} and removing R_G . Since the op amp input is high impedance, the attenuation is set by the resistor divider.

The inverting circuit of Figure 54 can be used as an attenuator by making R_G larger than R_F . The attenuation is simply the resistor ratio. For example a 10:1 attenuator can be implemented with $R_F = 1 \ k\Omega$ and $R_G = 10 \ k\Omega$.

Single Ended to Differential Amplifier

Figure 55 shows an amplifier circuit that is used to convert single-ended signals to differential, and provides gain and level shifting. This circuit can be used for converting signals to differential in applications like line drivers for CAT 5 cabling or driving differential input SAR and $\Delta\Sigma$ ADCs.

By setting $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT+} = G \times V_{IN} + V_{REF}$$
 and $V_{OUT-} = -G \times V_{IN} + V_{REF}$ Where: $G = 1 + \frac{R_F}{R_C}$

The differential signal gain of the circuit is 2x G, and V_{REF} provides a reference around which the output signal swings. The differential output signal is in-phase with the single ended input signal.

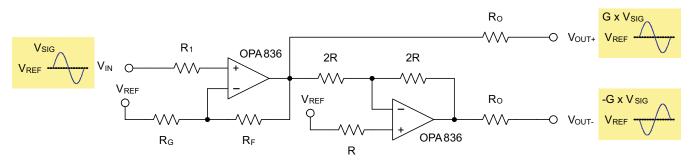


Figure 55. Single Ended to Differential Amplifier

Line termination on the output can be accomplished with resistors R_O. The impedance seen differential from the line will be 2x R_O. For example if 100 Ω CAT 5 cable is used with double termination, the amplifier is typically set for a differential gain of 2 V/V (6 dB) with R_F = 0 Ω (short) R_G = $\infty \Omega$ (open), 2R = 1 k Ω , R1 = 0 Ω , R = 499 Ω to balance the input bias currents, and R_O = 49.9 Ω for output line termination. This configuration is shown in Figure 56.

For driving a differential input ADC the situation is similar, but the output resistors, R_O, are typically chosen along with a capacitor across the ADC input for optimum filtering and settling time performance.



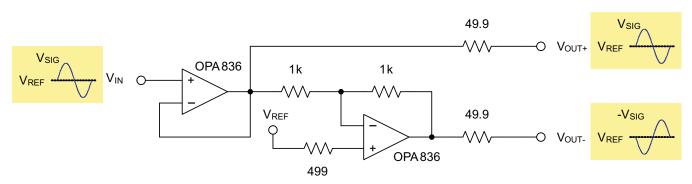


Figure 56. CAT 5 Line Driver with Gain = 2 V/V (6 dB)

Differential to Signal Ended Amplifier

Figure 57 shows a differential amplifier that is used to convert differential signals to single-ended and provides gain (or attenuation) and level shifting. This circuit can be used in applications like a line receiver for converting a differential signal from a CAT 5 cable to single-ended.

If we set $V_{IN+} = V_{CM} + V_{SIG+}$ and $V_{IN-} = V_{CM} + V_{SIG-}$, then

$$V_{OUT} = (V_{IN+} - V_{IN-}) \times \left(\frac{R_F}{R_G}\right) + V_{REF}$$
(4)

$$G = \frac{R_F}{D}$$

The signal gain of the circuit is set by: R_G , V_{CM} is rejected, and V_{REF} provides a level shift around which the output signal swings. The single ended output signal is in-phase with the differential input signal.

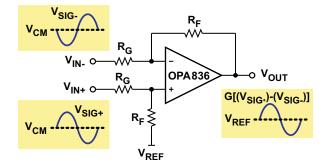


Figure 57. Differential to Single Ended Amplifier

Line termination can be accomplished with a resistor shunt across the input. The impedance seen differential from the line will be the resistor value in parallel with the amplifier circuit. For low gain and low line impedance the resistor value to add is approximately the impedance of the line. For example if 100 Ω CAT5 cable is used with a gain of 1 amplifier and R_F = R_G = 1 k Ω , adding a 100 Ω shunt across the input will give a differential impedance of 98 Ω ; this should be adequate for most applications.

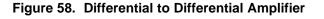
For best CMRR performance, resistors must be matched. A rule of thumb is CMRR \approx the resistor tolerance; so 0.1% tolerance will provide about 60 dB CMRR.

Differential to Differential Amplifier

Figure 58 shows a differential amplifier that is used to amplify differential signals. This circuit has high input impedance and is often used in differential line driver applications where the signal source is a high impedance driver like a differential DAC that needs to drive a line.

If we set $V_{IN\pm} = V_{CM} + V_{SIG\pm}$ then

$$V_{OUT \pm} = V_{IN\pm} \times \left(1 + \frac{2R_F}{R_G}\right) + V_{CM}$$
(5)
The signal gain of the circuit is set by:
combines two non-inverting amplifiers into one differential amplifier with the R_G resistor shared, which makes R_G effectively ½ its value when calculating the gain. The output signals are in-phase with the input signals.



Instrumentation Amplifier

Figure 59 is an instrumentation amplifier that combines the high input impedance of the differential to differential amplifier circuit and the common-mode rejection of the differential to single-ended amplifier circuit. This circuit is often used in applications where high input impedance is required like taps from a differential line or in cases where the signal source is a high impedance.

If we set $V_{IN+} = V_{CM} + V_{SIG+}$ and $V_{IN-} = V_{CM} + V_{SIG-}$, then

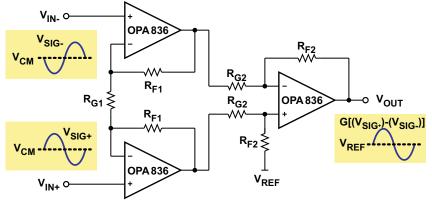
V_{IN+}

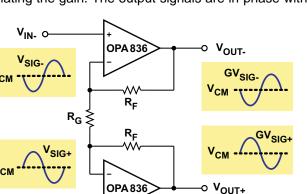
$$V_{OUT} = \left(V_{IN+} - V_{IN-}\right) \times \left(1 + \frac{2R_{F1}}{R_{G1}}\right) \left(\frac{R_{F2}}{R_{G2}}\right) + V_{REF}$$

The signal gain of the circuit is set by:

 $G = \left(1 + \frac{2R_{F1}}{R_{G1}}\right) \left(\frac{R_{F2}}{R_{G2}}\right), V_{CM} \text{ is rejected, and } V_{REF} \text{ provides a level shift around which the output signal is in-phase with the differential input signal.}$









www.ti.com

makes R_G

(5)

(6)



Integrated solutions are available, but the OPA836 provides a much lower power high frequency solution. For best CMRR performance, resistors must be matched. Assuming CMRR \approx the resistor tolerance; so 0.1% tolerance will provide about 60 dB CMRR.

Gain Setting with OPA836 RUN Integrated Resistors

The OPA836 RUN package option includes integrated gain setting resistors for smallest possible footprint on a printed circuit board ($\approx 2mm \times 2mm$). By adding circuit traces on the PCB, gains of +1, -1, -1.33, +2, +2.33, -3, +4, -4, +5, -5.33, +6.33, -7, +8 and inverting attenuations of -0.1429, -0.1875, -0.25, -0.33, -0.75 can be achieved.

Figure 60 shows a simplified view of how the OPA836IRUN integrated gain setting network is implemented. Table 1 shows the required pin connections for various non-inverting and inverting gains (reference Figure 53 and Figure 54). Table 2 shows the required pin connections for various attenuations using the inverting amplifier architecture (reference Figure 54). Due to ESD protection devices being used on all pins, the absolute maximum and minimum input voltage range, V_{S-} - 0.7V to V_{S+} + 0.7V, applies to the gain setting resistors, and so attenuation of large input voltages will require external resistors to implement.

The gain setting resistors are laser trimmed to 1% tolerance with nominal values of 1.6 k Ω , 1.2 k Ω , and 400 Ω . They have excellent temperature coefficient and gain tracking is superior to using external gain setting resistors. The 500 Ω and 1.5 pF capacitor in parallel with the 1.6 k Ω gain setting resistor provide compensation for best stability and pulse response.

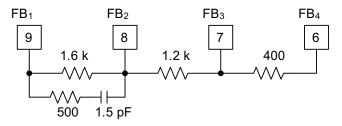


Figure 60. OPA836IRUN Gain Setting Network

Non-inverting Gain (Figure 53)	Inverting Gain (Figure 54)	Short Pins	Short Pins	Short Pins	Short Pins
1 V/V (0 dB)	-	1 to 9			-
2 V/V (6.02 dB)	-1 V/V (0 dB)	1 to 9	2 to 8	6 to GND	-
2.33 V/V (7.36 dB)	-1.33 V/V (2.5 dB)	1 to 9	2 to 8	7 to GND	-
4 V/V (12.04 dB)	-3 V/V (9.54 dB)	1 to 8	2 to 7	6 to GND	-
5 V/V (13.98 dB)	-4 V/V (12.04 dB)	1 to 9	2 to 7 or 8	7 to 8	6 to GND
6.33 V/V (16.03 dB)	-5.33 V/V (14.54 dB)	1 to 9	2 to 6 or 8	6 to 8	7 to GND
8 V/V (18.06 dB)	-7 V/V (16.90 dB)	1 to 9	2 to 7	6 to GND	-

Table 1. Gains Setting

Table 2. Attenuator Settings

Inverting Gain (Figure 54)	Short Pins	Short Pins	Short Pins	Short Pins
-0.75 V/V (-2.5 dB)	1 to 7	2 to 8	9 to GND	-
-0.333 V/V (-9.54 dB)	1 to 6	2 to 7	8 to GND	-
-0.25 V/V (-12.04 dB)	1 to 6	2 to 7 or 8	7 to 8	9 to GND
-0.1875 V/V (-14.54 dB)	1 to 7	2 to 6 or 8	6 to 8	9 to GND
-0.1429 V/V (-16.90 dB)	1 to 6	2 to 7	9 to GND	-



www.ti.com

Input Common-Mode Voltage Range

When the primary design goal is a linear amplifier, with high CMRR, it is important to not violate the input common-mode voltage range (V_{ICR}) of an op amp.

Common-mode input range low and high specifications in the table data use CMRR to set the limit. The limits are chosen to ensure CMRR will not degrade more than 3dB below its limit if the input voltage is kept within the specified range. The limits cover all process variations and most parts will be better than specified. The typical specifications are from 0.2 V below the negative rail to 1.1 V below the positive rail.

Assuming the op amp is in linear operation the voltage difference between the input pins is very small (ideally 0 V) and input common-mode voltage can be analyzed at either input pin and the other input pin is assumed to be at the same potential. The voltage at V_{IN+} is easy to evaluate. In non-inverting configuration, Figure 53, the input signal, V_{IN} , must not violate the V_{ICR} . In inverting configuration, Figure 53, the reference voltage, V_{REF} , needs to be within the V_{ICR} .

The input voltage limits have fixed headroom to the power rails and track the power supply voltages. For with single 5 V supply, the linear input voltage range is -0.2 V to 3.9 V and with 2.7 V supply it is -0.2 V to 1.6V. The delta from each power supply rail is the same in either case; -0.2 V and 1.1 V.

Output Voltage Range

The OPA836 and OPA2836 are rail-to-rail output (RRO) op amps. Rail-to-rail output typically means the output voltage can swing to within a couple hundred milli-volts of the supply rails. There are different ways to specify this; one is with the output still in linear operation and another is with the output saturated. Saturated output voltages are closer to the power supply rails than linear outputs, but the signal is not a linear representation of the input. Linear output is a better representation of how well a device performs when used as a linear amplifier. Both saturation and linear operation limits are affected by the current in the output, where higher currents lead to more loss in the output transistors.

Data in the ELECTRICAL SPECIFICATIONS tables list both linear and saturated output voltage specifications with $1k\Omega$ load. and show saturated voltage swing limits versus output load resistance and and show the output saturation voltage versus load current. Given a light load, the output voltage limits have nearly constant headroom to the power rails and track the power supply voltages. For example with 2 k Ω load and single 5 V supply the linear output voltage range is 0.15 V to 4.8 V and with 2.7 V supply it is 0.15 V to 2.5V. The delta from each power supply rail is the same in either case; 0.15 V and 0.2 V.

With devices like the OPA836 and OPA2836, where the input range is lower than the output range, it is typical that the input will limit the available signal swing only in non-inverting gain of 1. Signal swing in non-inverting configurations in gains > +1 and inverting configurations in any gain is generally limited by the output voltage limits of the op amp.

Split-Supply Operation (±1.25V to ±2.75V)

To facilitate testing with common lab equipment, the OPA836 EVM SLOU314 is built to allow for split-supply operation. This configuration eases lab testing because the mid-point between the power rails is ground, and most signal generators, network analyzers, oscilloscopes, spectrum analyzers and other lab equipment reference their inputs and outputs to ground.

Figure 61 shows a simple non-inverting configuration analogous to Figure 53 with ± 2.5 V supply and V_{REF} equal to ground. The input and output will swing symmetrically around ground. Due to its ease of use, split supply operation is preferred in systems where signals swing around ground, but it requires generation of two supply rails.



SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

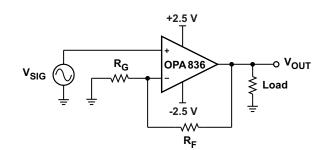


Figure 61. Split Supply Operation

Single-Supply Operation (2.5 V to 5.5 V)

Many newer systems use single power supply to improve efficiency and reduce the cost of the power supply. OPA836 and OPA2836 are designed for use with single-supply power operation and can be used with single-supply power with no change in performance from split supply as long as the input and output are biased within the linear operation of the device.

To change the circuit from split supply to single supply, level shift of all voltages by $\frac{1}{2}$ the difference between the power supply rails. For example, changing from ±2.5 V split supply to 5 V single supply is shown conceptually in Figure 62.

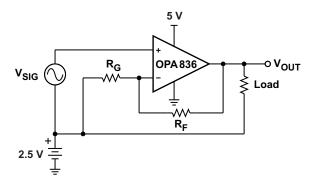


Figure 62. Single Supply Concept

A more practical circuit will have an amplifier or other circuit before to provide the bias voltage for the input and the output provides the bias for the next stage.

Figure 63 shows a typical non-inverting amplifier situation. With 5V single supply, a mid supply reference generator is needed to bias the negative side via R_G . To cancel the voltage offset that would otherwise be caused by the input bias currents, R_1 is chosen to be equal to R_F in parallel with R_G . For example if gain of 2 is required and $R_F = 1 \ k\Omega$, select $R_G = 1 \ k\Omega$ to set the gain and $R_1 = 499 \ \Omega$ for bias current cancellation. The value for C is dependent on the reference, but at least 0.1 μ F is recommended to limit noise.



www.ti.com

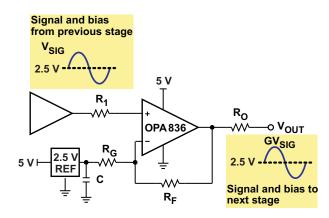


Figure 63. Non-Inverting Single Supply with Reference

Figure 64 shows a similar non-inverting single supply scenario with the reference generator replaced by the Thevenin equivalent using resistors and the positive supply. R_G' and R_G'' form a resistor divider from the 5 V supply and are used to bias the negative side with their parallel sum equal to the equivalent R_G to set the gain. To cancel the voltage offset that would otherwise be caused by the input bias currents, R_1 in is chosen to be equal to R_F in parallel with R_G'' in parallel with $R_G'' (R_1 = R_F ||R_G''| |R_G'')$. For example if gain of 2 is required and $R_F = 1 \ k\Omega$, selecting $R_G'' = R_G'' = 2 \ k\Omega$ gives equivalent parallel sum of 1 $k\Omega$, sets the gain to 2, and references the input to mid supply (2.5 V). R_1 is then set to 499 Ω for bias current cancellation. This can be lower cost, but note the extra current draw required in the resistor divider.

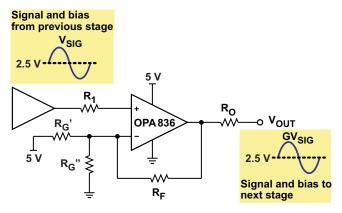


Figure 64. Non-Inverting Single Supply with Resistors

Figure 65 shows a typical inverting amplifier situation. With 5V single supply, a mid supply reference generator is needed to bias the positive side via R₁. To cancel the voltage offset that would otherwise be caused by the input bias currents, R₁ is chosen to be equal to R_F in parallel with R_G. For example if gain of -2 is required and R_F = 1 k Ω , select R_G = 499 Ω to set the gain and R₁ = 332 Ω for bias current cancellation. The value for C is dependent on the reference, but at least 0.1 µF is recommended to limit noise into the op amp.



SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

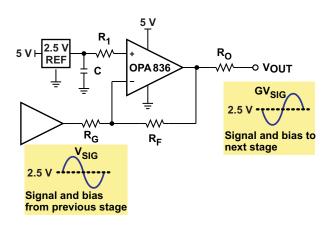


Figure 65. Inverting Single Supply with Reference

Figure 66 shows a similar inverting single supply scenario with the reference generator replaced by the Thevenin equivalent using resistors and the positive supply. R_1 and R_2 form a resistor divider from the 5 V supply and are used to bias the positive side. To cancel the voltage offset that would otherwise be caused by the input bias currents, set the parallel sum of R_1 and R_2 equal to the parallel sum of R_F and R_G . C should be added to limit coupling of noise into the positive input. For example if gain of -2 is required and $R_F = 1 \ k\Omega$, select $R_G = 499 \ \Omega$ to set the gain. $R_1 = R_2 = 665 \ \Omega$ for mid supply voltage bias and for op amp input bias current cancellation. A good value for C is 0.1 μ F. This can be lower cost, but note the extra current draw required in the resistor divider.

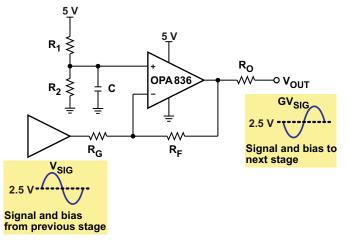


Figure 66. Inverting Single Supply with Resistors

Pulse Application with Single-Supply

For pulsed applications, where the signal is at ground and pulses to some positive or negative voltage, the circuit bias voltage considerations are different than with a signal that swings symmetrical about a reference point and the circuit configuration should be adjusted accordingly. Figure 67 shows a pulsed situation where the signal is at ground (0 V) and pulses to a positive value.

TEXAS INSTRUMENTS

www.ti.com

SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

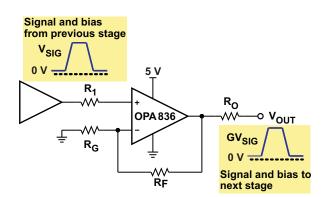


Figure 67. Non-Inverting Single Supply with Pulse

If the input signal pulses negative from ground, an inverting amplifier is more appropriate as shown in Figure 68. A key consideration in both non-inverting and inverting cases is that the input and output voltages are kept within the limits of the amplifier, and since the V_{ICR} of the OPA836 includes the negative supply rail, the op amp lends itself to this application.

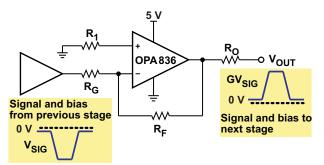


Figure 68. Inverting Single Supply with Pulse

Power-Down Operation

The OPA836 and OPA2836 include a power-down mode. Under logic control, the amplifiers can be switched from normal <u>op</u>eration to a standby current of <1.5 μ A. When the PD pin is connected high, the amplifier is active. Connecting PD pin low disables the amplifier, and places the output in a high impedance state. Note: the op amp's output in gain of +1 is high impedance similar to a 3-state high impedance gate, but in other gains the feedback network is a parallel load.

The PD pin must be actively driven high or low and should not be left floating. If the power-down mode is not used, PD should be tied to the positive supply rail.

 \overline{PD} logic states are TTL with reference to the negative supply rail, V_S. When the op amp is powered from single supply and ground, driving from logic devices with similar V_{DD} voltages to the op amp should not require any special consideration. When the op amp is powered from split supply, V_S is below ground and an open collector type of interface with pull-up resistor is more appropriate. Pull-up resistor values should be lower than 100k and the drive logic should be negated due to the inverting action of an open collector gate.



Low Power Applications and the Effects of Resistor Values on Bandwidth

The OPA836 and OPA2836 are designed for the nominal value of R_F to be 1 k Ω in gains other than +1. This gives excellent distortion performance, maximum bandwidth, best flatness, and best pulse response. It also loads the amplifier. For example; in gain of 2 with $R_F = R_G = 1 k\Omega$, R_G to ground, and $V_{OUT} = 4 V$, 2 mA of current will flow through the feedback path to ground. In gain of +1, R_G is open and no current will flow to ground. In low power applications, it is desirable to reduce this current by increasing the gain setting resistors values. Using larger value gain resistors has two primary side effects (other than lower power) due to their interaction with parasitic circuit capacitance.

- 1. Lowers the bandwidth.
- 2. Lowers the phase margin
 - (a) This will cause peaking in the frequency response.
 - (b) And will cause over shoot and ringing in the pulse response.

Figure 69 shows the small signal frequency response on OPA836EVM for non-inverting gain of 2 with R_F and R_G equal to 1 k Ω , 10 k Ω , and 100k Ω . The test was done with $R_L = 1 k\Omega$. Due to loading effects of R_L , lower values may reduce the peaking, but higher values will not have a significant effect.

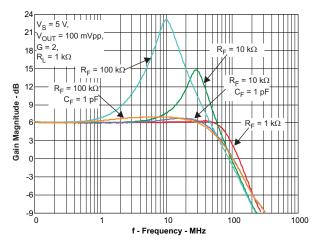


Figure 69. Frequency Response with Various Gain Setting Resistor Values

As expected, larger value gain resistors cause lower bandwidth and peaking in the response (peaking in frequency response is synonymous with overshoot and ringing in pulse response). Adding 1 pF capacitors in parallel with R_F helps compensate the phase margin and restores flat frequency response. Figure 70 shows the test circuit used.

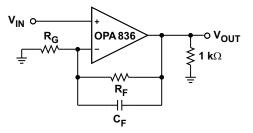


Figure 70. G = 2 Test Circuit for Various Gain Setting Resistor Values



Driving Capacitive Loads

The OPA836 and OPA2836 can drive up to a nominal capacitive load of 2.2 pF on the output with no special consideration. When driving capacitive loads greater than this, it is recommended to use a small resister (R_0) in series with the output as close to the device as possible. Without R_0 , capacitance on the output will interact with the output impedance of the amplifier causing phase shift in the loop gain of the amplifier that will reduce the phase margin. This will cause peaking in the frequency response and overshoot and ringing in the pulses response. Interaction with other parasitic elements may lead to instability or oscillation. Inserting R_0 will isolate the phase shift from the loop gain path and restore the phase margin; however, it will also limit the bandwidth.

Figure 71 shows the test circuit and shows the recommended values of R_0 versus capacitive loads, C_L . See for frequency response with various values.

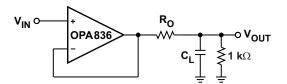


Figure 71. R_o versus C_L Test Circuit

Active Filters

The OPA836 and OPA2836 can be used to design active filters. Figure 73 and Figure 72 show MFB and Sallen-Key circuits designed using FilterPro[™] http://focus.ti.com/docs/toolsw/folders/print/filterpro.html to implement 2nd order low-pass butterworth filter circuits. Figure 74 shows the frequency response.

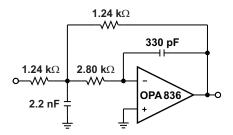


Figure 72. MFB 100kHz 2nd Order Low-Pass Butterworth Filter Circuit

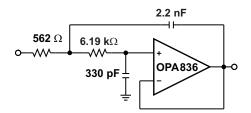


Figure 73. Sallen-Key 100kHz 2nd Order Low-Pass Butterworth Filter Circuit



SLOS712E – JANUARY 2011 – REVISED SEPTEMBER 2013

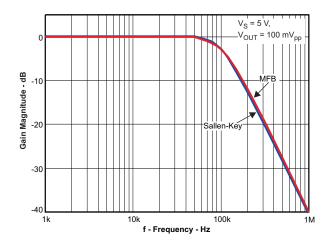


Figure 74. MFB and Sallen-Key 2_{nd} Order Low-Pass Butterworth Filter Response

MFB and Sallen-Key filter circuits offer similar performance. The main difference is the MFB is an inverting amplifier in the pass band and the Sallen-Key is non-inverting. The primary pro for each is the Sallen-Key in unity gain has no resistor gain error term, and thus no sensitivity to gain error, while the MFB has inherently better attenuation properties beyond the bandwidth of the op amp.

Audio Frequency Performance

The OPA836 and OPA2836 provide excellent audio performance with very low quiescent power. To show performance in the audio band, a 2700 series Audio Analyzer from Audio Precision was used to test THD+N and FFT at $1V_{RMS}$ output voltage. Figure 75 is the test circuit used. Note the 100pF capacitor to ground on the input helped to decouple noise pick up in the lab and improved noise performance.

Figure 76 shows the THD+N performance with $100k\Omega$ and 300Ω loads, with A-weighting, and with no weighting. Both loads show similar performance. With no weighting the THD+N performance is dominated by the noise whereas A-weighting provides filtering that improves the noise.

Figure 77 and Figure 78 show FFT output with a 1 kHz tone and $100k\Omega$ and 300Ω loads. To show relative performance of the device versus the test set, one channel has the OPA836 in line between generator output and analyzer input and the other channel is in "Gen Mon" loopback mode, which internally connects the signal generator to the analyzer input. With 100 k Ω load, Figure 77, the curves are basically indistinguishable from each other except for noise, which means the OPA836 cannot be directly measured. With 300 Ω load, Figure 78, the main difference between the curves is OPA836 shows slightly higher even order harmonics, but odd order is masked by the test set performance.

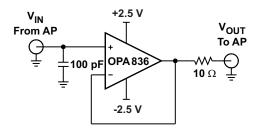


Figure 75. OPA836 AP Analyzer Test Circuit

OPA836 OPA2836



www.ti.com

SLOS712E – JANUARY 2011 – REVISED SEPTEMBER 2013

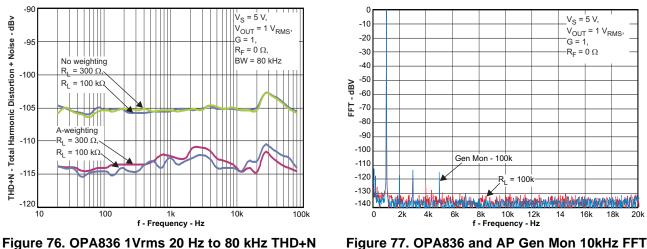
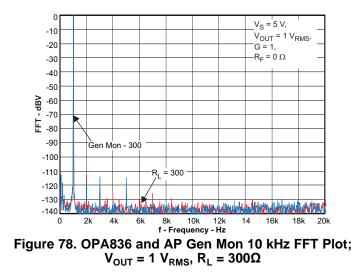


Figure 77. OPA836 and AP Gen Mon 10kHz FFT Plot; V_{OUT} = 1 V_{RMS} , R_L = 100 k Ω



ADC Driver Performance

The OPA836 provides excellent performance when driving high performance delta-sigma ($\Delta\Sigma$) and successive approximation register (SAR) ADCs in low power audio and industrial applications.



OPA836

OPA2836

www.ti.com

OPA836 and ADS8326 Combined Performance

To show achievable performance, the OPA836 is tested as the drive amplifier for the ADS8326. The ADS8326 is a 16-bit, micro power, SAR ADC with pseudo-differential inputs and sample rates up to 250 kSPS. It offers excellent noise and distortion performance in a small 8-pin SOIC or VSSOP (MSOP) package. Low power and small size make the ADS8326 and OPA836 an ideal solution for portable and battery-operated systems, for remote data-acquisition modules, simultaneous multichannel systems, and isolated data acquisition.

The circuit shown in Figure 79 is used to test the performance, Figure 80 is the FFT plot with 10 kHz input frequency showing the spectral performance, and the tabulated AC analysis results are in Table 3.

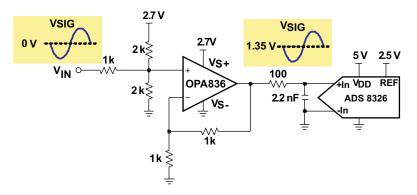


Figure 79. OPA836 and ADS8326 Test Circuit

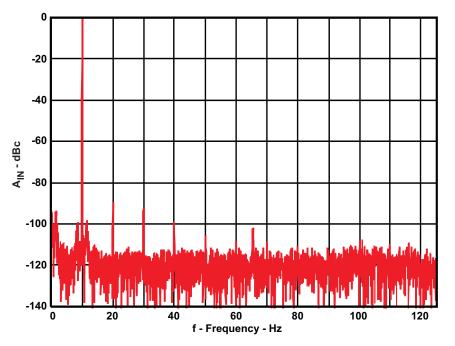


Figure 80. ADS8326 and OPA836 10kHz FFT

			-		
Tone (Hz)	Signal (dBFS)	SNR (dBc)	THD (dBc)	SINAD (dBc)	SFDR (dBc)
10k	-0.85	83.3	-86.6	81.65	88.9

SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013



Page

Page

Layout Recommendations

The OPA836 EVM (SLOU314) should be used as a reference when designing the circuit board. It is recommended to follow the EVM layout of the external components near to the amplifier, ground plane construction, and power routing as closely as possible. General guidelines are:

- 1. Signal routing should be direct and as short as possible into an out of the op amp.
- 2. The feedback path should be short and direct avoiding vias if possible especially with G = +1.
- 3. Ground or power planes should be removed from directly under the amplifier's negative input and output pins.
- 4. A series output resistor is recommended to be placed as near to the output pin as possible. See "Recommended Series Output Resistor vs. Capacitive Load" () for recommended values given expected capacitive load of design.
- 5. A 2.2 µF power supply decoupling capacitor should be placed within 2 inches of the device and can be shared with other op amps. For spit supply, a capacitor is required for both supplies.
- 6. A 0.1 μF power supply decoupling capacitor should be placed as near to the power supply pins as possible. Preferably within 0.1 inch. For split supply, a capacitor is required for both supplies.
- 7. The PD pin uses TTL logic levels. If not used it should tied to the positive supply to enable the amplifier. If used, it must be actively driven. A bypass capacitor is not necessary, but can be used for robustness in noisy environments.

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (October 2011) to Revision E

•	Added OPA2836 RMC package to document	1
•	Added RMC package to second bullet in <i>Description</i> section	1
•	Deleted Packaging/Ordering Information table, leaving only note to POA	2
•	Added OPA2836 RMC package to Thermal Information table	2
•	Added OPA2839 RMC designator to OPA2836 RUN pin out diagram	9
•	Added OPA2836 RMC pin definitions to Pin Functions table	11

Changes from Revision A (March 2011) to Revision B

•	Changed OPA836 from product preview t	production data	1
---	---------------------------------------	-----------------	---

Copyright © 2011-2013, Texas Instruments Incorporated

..... 5

SLOS712E - JANUARY 2011 - REVISED SEPTEMBER 2013

Replaced the TBD values in the Thermal Information table	
Changed - Channel to channel crosstalk (OPA2836) Typ value From: TBD To: -120 dB	
Changed the Common-mode rejection ratio Min value From: 94 dB To: 91 dB	
Added GAIN SETTING RESISTORS (OPA836IRUN ONLY)	
 Changed the Quiescent operating current (T_A = 25°C) Min value From: 0.8 mA To: 0.7 mA	
Changed the Power supply rejection (±PSRR) Min value From: 95 dB To: 91 dB	
Changed the Powerdown pin bias current CONDITIONS From: PD = 0.7V To: PD = 0.5V	
Changed the Powerdown quiescent current CONDITIONS From: PD = 0.7V To: PD = 0.5V	
Changed - Channel to channel crosstalk (OPA2836) Typ value From: TBD To: -120 dB	
Changed the Common-mode rejection ratio Min value From: 97 dB To: 94 dB	
Added GAIN SETTING RESISTORS (OPA836IRUN ONLY)	
 Changed the Quiescent operating current (T_A = 25°C) Min value From: 0.9 mA To: 0.8 mA	
Changed the Power supply rejection (±PSRR) Min value From: 97 dB To: 94 dB	
Changed the Powerdown quiescent current CONDITIONS From: PD = 0.7V To: PD = 0.5V	
Changed the Powerdown quiescent current CONDITIONS From: PD = 0.7V To: PD = 0.5V	

Added the "The OPA836 RUN package..." text to the DESCRIPTION 1 Removed Product Preview from all devices except OPA836IRUNT and OPA836IRUNR 2

Added Figure Crosstalk vs Frequency 14

Changes from Revision C (September 2011) to Revision D

Page

•	Removed Product Preview from OPA836IRUNT and OPA836IRUNR	2
•	Changed Resistor Temperature Coefficient Typ value From: TBD To: <10	5
•	Changed Quiescent operating current To: Quiescent operating current per amplifer	5
	Changed Resistor Temperature Coefficient Typ value From: TBD To: <10	
•	Changed Quiescent operating current To: Quiescent operating current per amplifer	8

STRUMENTS

Changes from Revision B (May 2011) to Revision C

www.ti.com

Page



2-Apr-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	•	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
OPA2836ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IDGS	ACTIVE	VSSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IDGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IRMCR	ACTIVE	UQFN	RMC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IRMCT	ACTIVE	UQFN	RMC	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IRUNR	ACTIVE	QFN	RUN	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA2836IRUNT	ACTIVE	QFN	RUN	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	2836	Samples
OPA836IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	QTL	Samples
OPA836IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	QTL	Samples
OPA836IRUNR	ACTIVE	QFN	RUN	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	836	Samples
OPA836IRUNT	ACTIVE	QFN	RUN	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	836	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.



www.ti.com

2-Apr-2015

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and package, or 2) lead-based die adhesive used between the die and package, or 2) lead-based die adhesive used between the die and package.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA2836IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2836IRMCR	UQFN	RMC	10	3000	180.0	9.5	2.3	2.3	1.1	2.0	8.0	Q2
OPA2836IRMCT	UQFN	RMC	10	250	180.0	9.5	2.3	2.3	1.1	2.0	8.0	Q2
OPA2836IRUNR	QFN	RUN	10	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA2836IRUNT	QFN	RUN	10	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA836IDBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
OPA836IDBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
OPA836IRUNR	QFN	RUN	10	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA836IRUNT	QFN	RUN	10	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

Texas Instruments

www.ti.com

PACKAGE MATERIALS INFORMATION

4-Sep-2014



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA2836IDR	SOIC	D	8	2500	340.5	338.1	20.6
OPA2836IRMCR	UQFN	RMC	10	3000	205.0	200.0	30.0
OPA2836IRMCT	UQFN	RMC	10	250	205.0	200.0	30.0
OPA2836IRUNR	QFN	RUN	10	3000	210.0	185.0	35.0
OPA2836IRUNT	QFN	RUN	10	250	210.0	185.0	35.0
OPA836IDBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
OPA836IDBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
OPA836IRUNR	QFN	RUN	10	3000	210.0	185.0	35.0
OPA836IRUNT	QFN	RUN	10	250	210.0	185.0	35.0

DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
 - A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
 - E Falls within JEDEC MO-178 Variation AB, except minimum lead width.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE

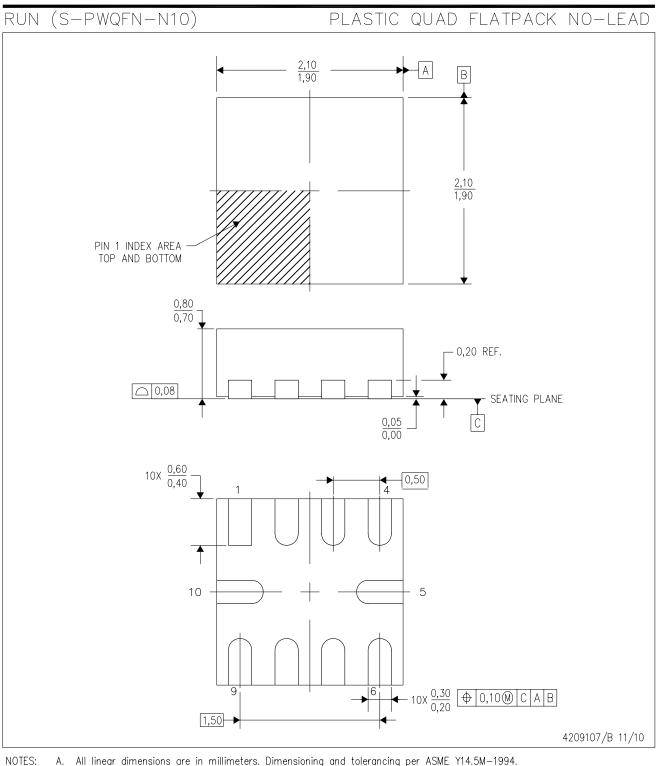


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



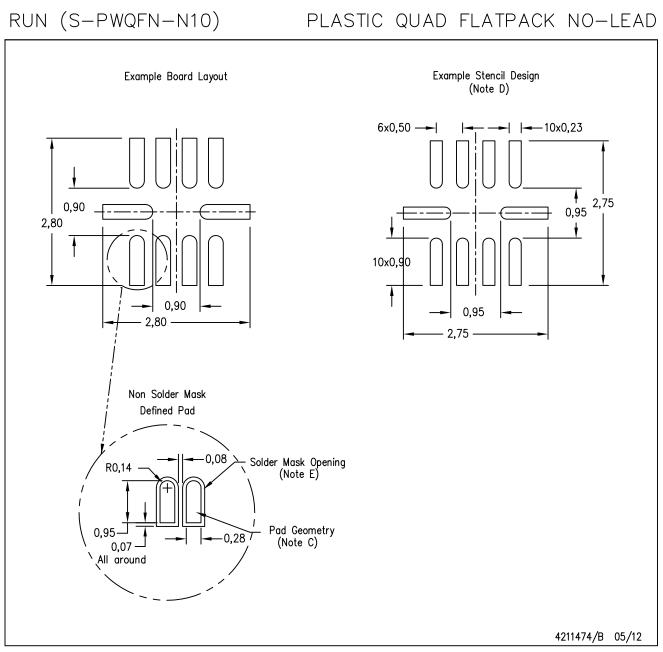
MECHANICAL DATA



A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- В. This drawing is subject to change without notice.
- C. Quad Flatpack, No-Leads (QFN) package configuration.



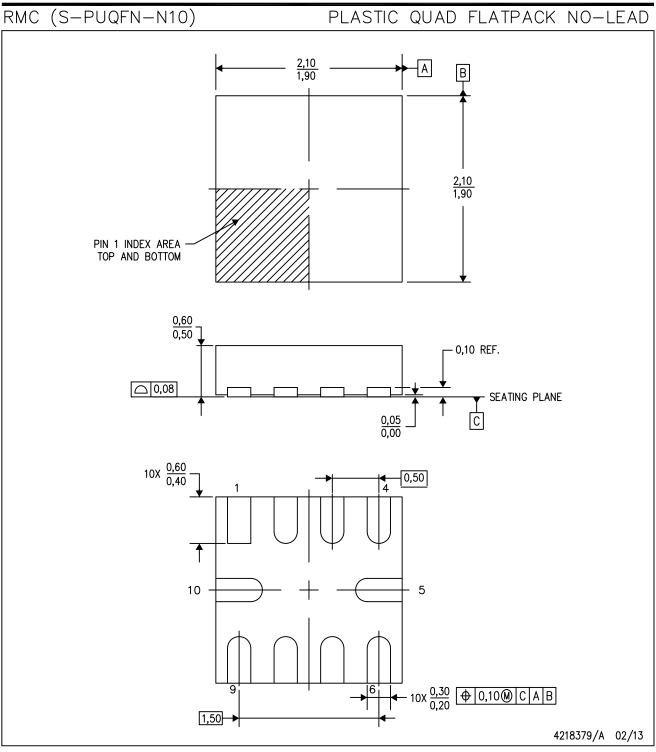


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 E. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



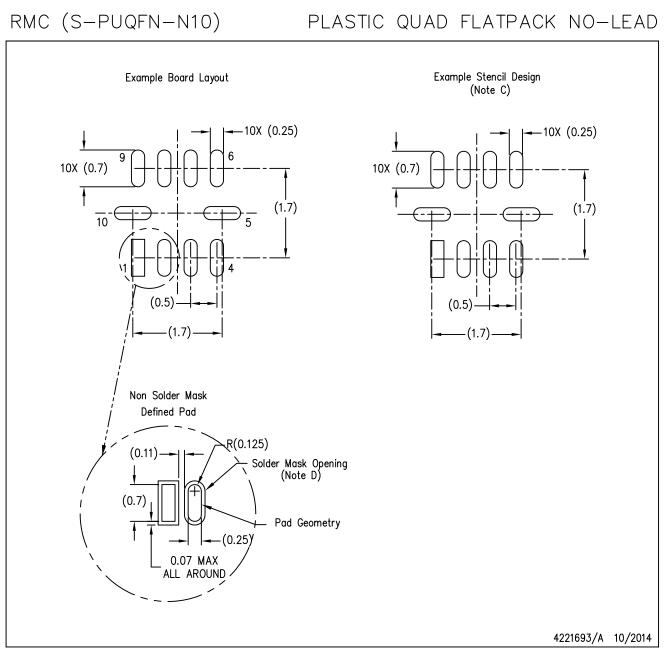
MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-Leads (QFN) package configuration.





NOTES: A. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only.

- B. This drawing is subject to change without notice.
- C. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ctivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2015, Texas Instruments Incorporated